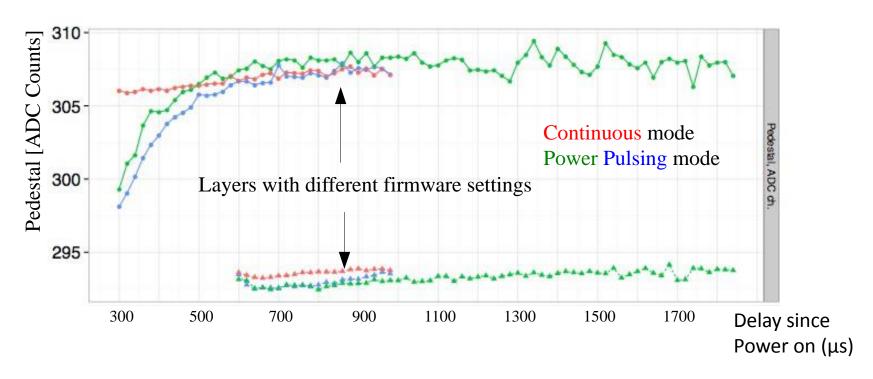
# Beam Test result of SiECAL ramp-up time of electronics under PP operation

2014/3/20
CALICE Meeting @ Argonne
Yuji Sudo (Kyushu University)
SiECAL group

# Power pulsing – "ramp-up" time (reminder)

 Analysis of detector response as function of delay between enabling of bias currents and signal arrival



Several channels are merged in this plot

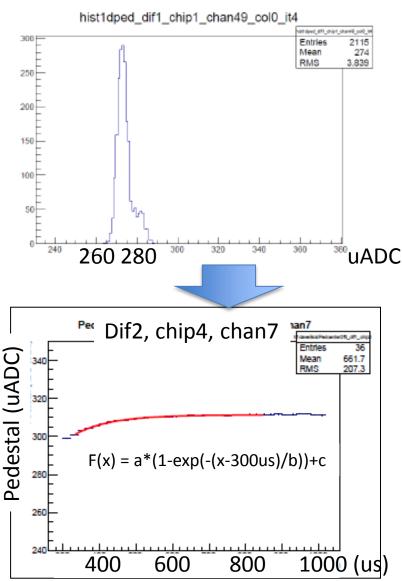
#### Pedestal position and time constant

• MIP run (run0005, PP)

- Make pedestal plots in 20us time window
- Fit pedestal peak with Gaussian (Mean +- 5bin)

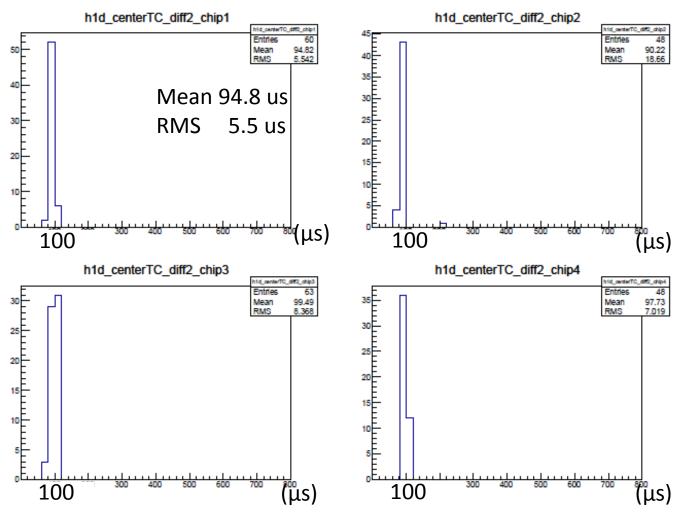


Fit the plot of pedestal vs time with
 F(x) = a\*(1-exp(-(x-300us)/b))+c



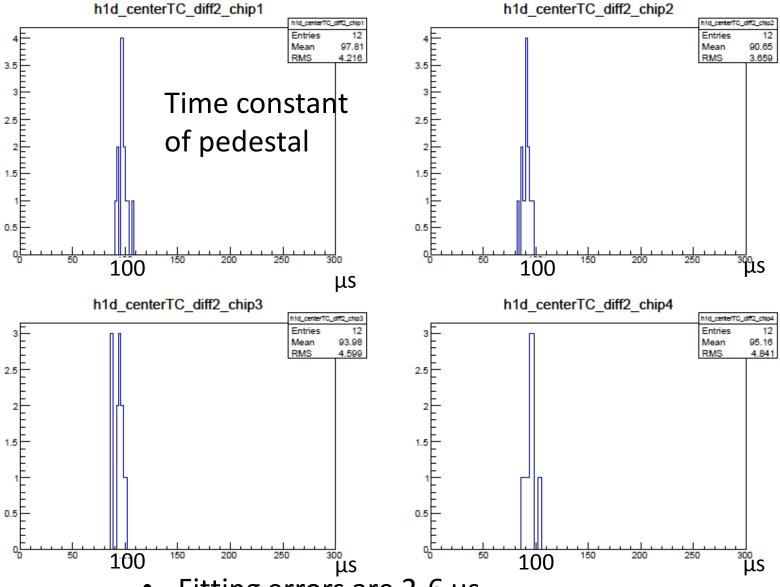
# Time constant of pedestal center value of all channel in a slab

MIP run (run0005, PP), all active and fitted channels



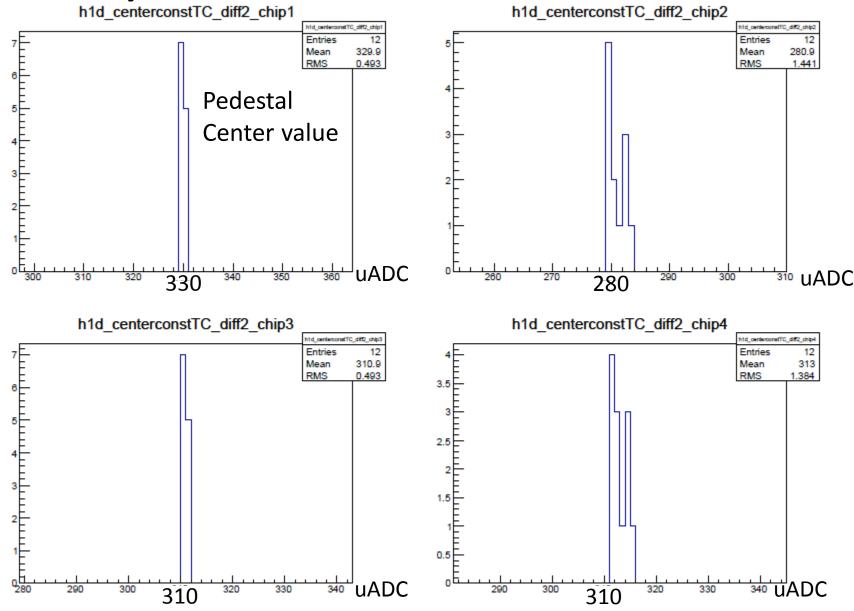
Time constant is distributed around 100 us

### Run by Run difference: Channel 12



- Fitting errors are 2-6 us
- Ramp-up time is stable (~100 μs)

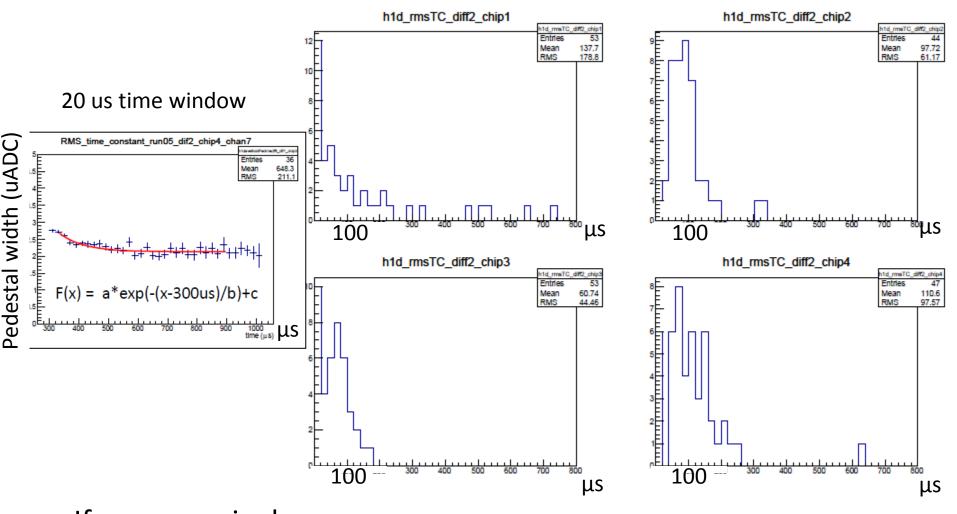
### Run by Run difference: Channel 12



Activity of digital lines increases a fluctuation of pedestal position

#### Time constant of pedestal width

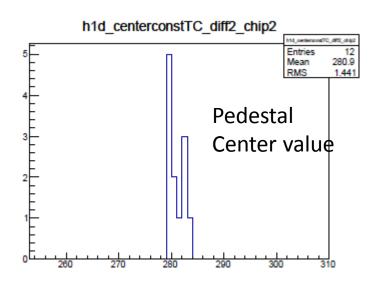
MIP run (run0005, PP), all active and fitted channels

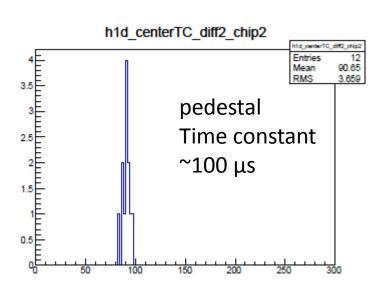


• If we use a single run, it is difficult to estimate a time dependence of pedestal width

### Summary

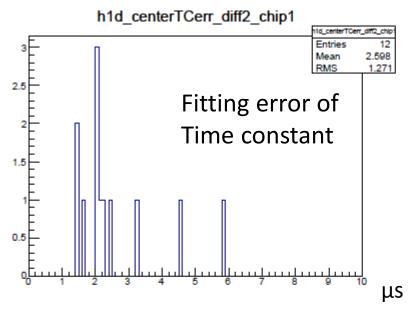
- Checked the run by run fluctuation of pedestal position
- Data taken under Power Pulsing operation
- Fluctuation of pedestal position is increased by activity of digital lines
- Ramp-up time is stable (~100 μs)
- Ramp-up time probably can be estimated from the structure of circuit

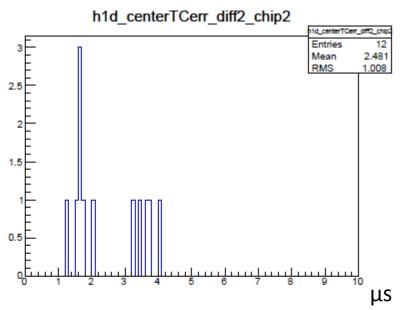


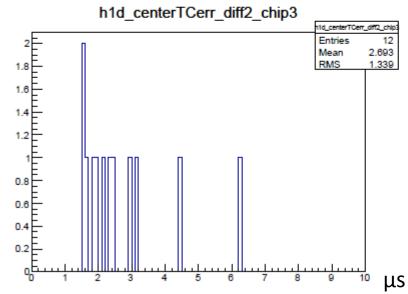


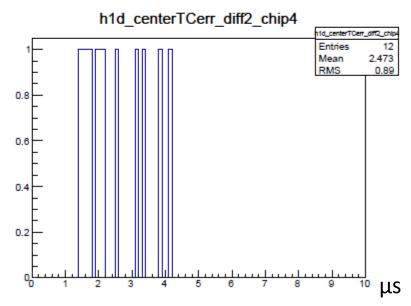
## Backup

## Run by Run difference: Channel 12





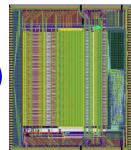


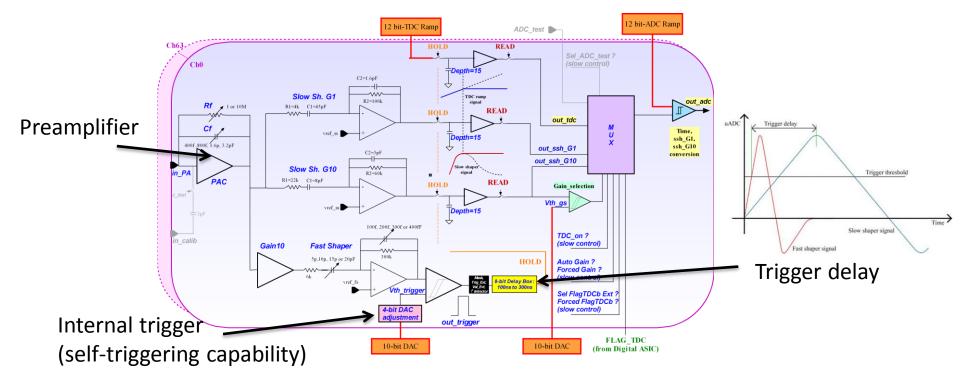


#### Front end electronics: SKIROC

#### SKIROC (Silicon Kalorimeter Integrated Read Out Chip)

- Size 7.5 mm x 8.7 mm, 64 channels
- Variable gain charge amp, 12-bit Wilkinson ADC, digigal logic
- Large dynamic range (~2500 MIPs), low noise (~1/10 of a MIP)
- Auto-trigger
- Low Power: (25 μW/ch) power pulsing





#### Test beams with fabricated layers

## Layer design for beam tests Integrated FE electronics

#### Conservative ASU design for beam test

- 1 Si Wafer with 256 pixels of 5x5 mm2 and thickness of 325  $\mu m$
- Wafer glued onto PCB
- 4 ASICs in PQFP package
- Up to 10 layers

#### Test program

- 2012: Commissioning
  - Test of highly integrated electronics in continuous power mode
- 2013: Test of power pulsing Test in magnetic field



